

AF 12881
#18 (B)
6/6/03
REASON UNDER 37 C.F.R. § 1.116
EXPEDITED PROCEDURE
EXAMINING GROUP 2881



PATENT
DKT. NO.: 29273/502

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANTS : Hajime KAWANO, et al.

SERIAL NO. : 09/315,988

FILED : May 21, 1999

FOR : ELECTRON BEAM LITHOGRAPHY SYSTEM

GROUP ART : 2881

EXAMINER : Kalimah Fernandez

COMMISSIONER FOR PATENTS

P.O. BOX 1450

Alexandria, VA 22313-1450

RECEIVED
JUN -2 2003
TECHNOLOGY CENTER 2800

RECEIVED
JUN 30 2003

AMENDMENT

Sir:

In response to the office action dated January 29, 2003, the due date being extended by the attached Petition for Extension of Time, please amend the above-identified application as follows:

IN THE CLAIMS

Please amend claim 1 as follows:

1. (Twice) An electron beam lithography system comprising:
exposure map creating means which, based on positional relations between meshes
dividing a region to be rendered by an electron beam on the one hand and shots to be rendered by
said electron beam on the other hand, creates an exposure map by calculating an area density
from a shot area included in each of said meshes; and

proximity effect correcting means for correcting a level of exposure for each of said shots
by referencing said exposure map so that each shot is exposed at the corrected level;